Wideband differential digital controlled variable gain amplifierRev. 04 — 14 August 2008Product data sheet

1. General description

The TDA9901 is a wideband, low-noise amplifier with differential inputs and outputs. The TDA9901 incorporates an Automatic Gain Control (AGC) function with digital control. The TDA9901 is optimized for fast switching between different gain settings, preserving small phase and amplitude error.

The TDA9901 presents an excellent combination of low noise and good linearity for a wide input frequency range. The TDA9901 is optimized for processing Input Frequency (IF) signals. It is also suited for many other applications as a general purpose digitally controlled variable gain amplifier.

The TDA9901 is able to operate from 4.75 V to 5.25 V supply for the analog part and from 3.0 V to 5.25 V for the digital part.

2. Features

- 130 MHz, -3 dB small signal bandwidth
- Digitally controlled gain
- Transistor-Transistor Logic (TTL) and CMOS compatible digital inputs (3.3 V or 5 V)
- TTL single-ended or differential clock input with Positive Emitter-Coupled Logic (PECL) compatibility
- 24 dB gain control range
- Four steps of 6 dB plus 6 dB fixed gain
- 30 dB gain maximum
- High impedance differential inputs
- Low impedance differential inputs
- High power supply rejection
- 125 nV/√Hz output voltage noise density at 30 dB gain
- Fast gain settling
- Dual control modes: transparent or latched

3. Applications

- Linear AGC systems
- Wireless infrastructure
- Fixed network
- Instrumentation
- Multipurpose amplifier
- Driver for differential ADCs (e.g. ADC1206S040/055/070 and ADC1006055/070)



4. Quick reference data

Table 1. Quick reference data

 $V_{DDA} = V11$ to V12 = 4.75 V to 5.25 V; $V_{DDD} = V18$ to V17 = 3.0 V to 5.25 V; V_{SSA} and V_{SSD} shorted together; $T_{amb} = -40$ °C to +85 °C; typical values measured at $V_{CCA} = 5.0$ V; $V_{CCD} = 3.3$ V and $T_{amb} = 25$ °C unless otherwise specified [1].

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DDA}	analog supply voltage		4.75	5.0	5.25	V
V _{DDD}	digital supply voltage		3.0	3.3	5.25	V
I _{DDA}	analog supply current		-	30	36	mA
I _{DDD}	digital supply current		-	3.0	5.0	mA
G _{min} ı	minimum gain	DC input:				
		$T_{amb} = 25 \ ^{\circ}C$	5.78	6.11	6.40	dB
		all temperatures	5.7	6.11	6.46	dB
G _{max}	maximum gain	DC input:				
		$T_{amb} = 25 \ ^{\circ}C$	29.9	30.5	30.9	dB
		all temperatures	29.3	30.5	31.5	dB
B_3dB	-3 dB bandwidth	$ V_{o(dif)(p-p)} = 0.125 \text{ V}; $	110	130	-	MHz
P _{tot}	total power dissipation		-	160	216	mW

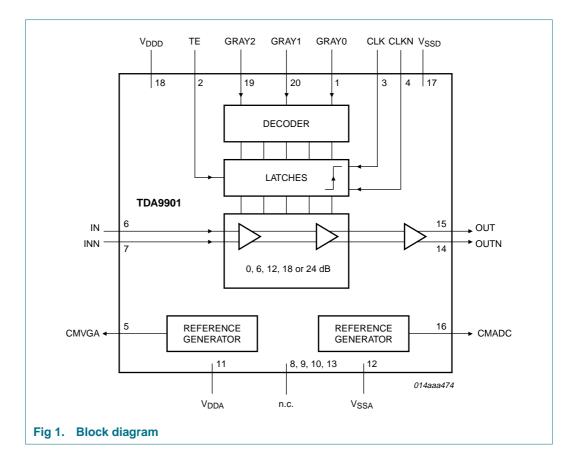
[1] Due to on-chip regulator behavior a warm-up time of 1 minute (typical) is recommended for optimal performance.

5. Ordering information

Table 2. Orderin	g information		
Type number	Package		
	Name	Description	Version
TDA9901TS	SSOP20	plastic shrink small outline package; 20 leads; body width 4.4 mm	SOT266-1

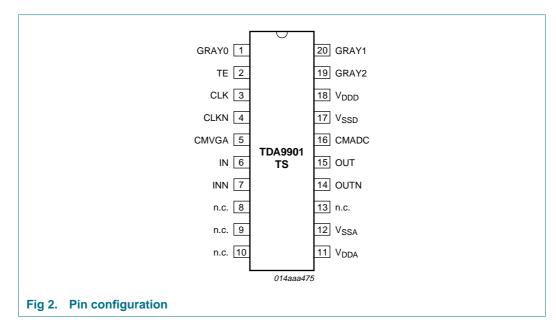
Wideband differential digital controlled variable gain amplifier

6. Block diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
GRAY0	1	digital control signal bit 0 input (Least Significant Bit (LSB))
TE	2	transparent enable input
CLK	3	clock input for gain control setting
CLKN	4	inverting clock input for gain control setting (active LOW)
CMVGA	5	regulator output common mode VGA input
IN	6	non-inverting analog input
INN	7	inverting analog input (active LOW)
n.c.	8	not connected
n.c.	9	not connected
n.c.	10	not connected
V_{DDA}	11	analog supply voltage
V _{SSA}	12	analog ground
n.c.	13	not connected
OUTN	14	inverting analog output (active LOW)
OUT	15	non-inverting analog output
CMADC	16	regulator output common mode ADC input
V _{SSD}	17	digital ground

Wideband differential digital controlled variable gain amplifier

Table 3.	Pin description continued				
Symbol	Pin	Description			
V _{DDD}	18	digital supply voltage			
GRAY2	19	digital control signal bit 2 input (Most Significant Bit (MSB))			
GRAY1	20	digital control signal bit 1 input			

Functional description 8.

The TDA9901 provides a digitally controlled variable gain function for high-frequency applications.

The TDA9901 can be operated in two different modes, depending on the value at pin TE. When TE is at logic 1, the gain can be instantly controlled when the clock signal is HIGH (transparent mode). The gain is fixed during the LOW period of the clock. When TE is at logic 0 the gain of the TDA9901 is changed at the rising edge of the clock signal.

Limiting values 9.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DDA}	analog supply voltage		-0.3	+7.0	V
V _{DDD}	digital supply voltage		-0.3	+7.0	V
ΔV_{DD}	supply voltage difference	$V_{DDA} - V_{DDD}$	-0.1	+4.0	V
VI	input voltage		-0.3	+7.0	V
lo	output current		-	10	mA
T _{stg}	storage temperature		-55	+150	°C
T _{amb}	ambient temperature		-40	+85	°C
Ti	junction temperature		-	150	°C

10. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Value	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	120	K/W

11. Characteristics

Table 6. Characteristics

 $V_{DDA} = V11$ to V12 = 4.75 V to 5.25 V; $V_{DDD} = V18$ to V17 = 3.0 V to 5.25 V; V_{SSA} and V_{SSD} shorted together; $T_{amb} = -40$ °C to +85 °C; typical values measured at $V_{CCA} = 5.0$ V; $V_{CCD} = 3.3$ V and $T_{amb} = 25$ °C unless otherwise specified [1].

<u>[1]</u>						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Supplies						
V _{DDA}	analog supply voltage		4.75	5.0	5.25	V
V _{DDD}	digital supply voltage		3.0	3.3	5.25	V
ΔV_{DD}	supply voltage difference	V _{DDA} – V _{DDD}	-0.2	-	+2.5	V
I _{DDA}	analog supply current		-	30	36	mA
I _{DDD}	digital supply current		-	3.0	5.0	mA
P _{tot}	total power dissipation		-	160	216	mW
Variable ga	in amplifier transfer chara	acteristics				
B_3dB	-3 dB bandwidth		110	130	-	MHz
t _{d(grp)}	group delay time	up to $f_i = 20 \text{ MHz}$; minimum gain; $T_{amb} = 25 \text{ °C}$	-	2.5	-	ns
$\Delta t_{d(grp)}$	group delay time variation	6 dB gain step; T _{amb} = 25 °C	-	-	300	ps
t _s	settling time	10 % to 90 % maximum output transition; $C_{L(max)} = 5 \text{ pF}$ on each output; $T_{amb} = 25 \text{ °C}$	-	-	3.6	ns
G _{step}	step of gain	DC input:				
		$T_{amb} = 25 \ ^{\circ}C$	5.88	6.09	6.28	dB
		all temperatures	5.6	6.09	6.56	dB
G _{min}	minimum gain	DC input:				
		$T_{amb} = 25 \ ^{\circ}C$	5.78	6.11	6.40	dB
		all temperatures	5.7	6.11	6.46	dB
G _{max}	maximum gain	DC input:				
		$T_{amb} = 25 \ ^{\circ}C$	29.9	30.5	30.9	dB
		all temperatures	29.3	30.5	31.5	dB
ΔG/ΔT	gain variation with	minimum gain	-	-1.0	-	mdB/°C
	temperature	maximum gain	-	-7.5	-	mdB/°C
$\Delta G / \Delta V_{CC}$	gain variation with supply voltage	minimum gain	-	15	25	mdB/V
∆V _{i(offset)}	offset input voltage variation	6 dB gain step	-	0.8	-	mV
NF	noise figure	$R_s = 100 \ \Omega; f_i = 20 \ MHz$				
		minimum gain	-	29.1	-	dB
		maximum gain	-	9.9	-	dB

Table 6. Characteristics ...continued

 $V_{DDA} = V11$ to V12 = 4.75 V to 5.25 V; $V_{DDD} = V18$ to V17 = 3.0 V to 5.25 V; V_{SSA} and V_{SSD} shorted together; $T_{amb} = -40$ °C to +85 °C; typical values measured at $V_{CCA} = 5.0$ V; $V_{CCD} = 3.3$ V and $T_{amb} = 25$ °C unless otherwise specified [1].

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
V _{n(o)(eq)}	equivalent output noise	R_s = 100 Ω ; f _i = 20 MHz; T_{amb} = 25 °C					
	voltage	G = 6 dB	-	75	-	nV/√H:	
		G = 12 dB	-	82	-	nV/√H:	
		G = 18 dB	-	97	-	nV/√H:	
		G = 24 dB	-	91	-	nV/√H:	
		G = 30 dB	-	124	-	nV/√H:	
PSRR	power supply rejection	minimum gain; V _{DDA}					
	ratio	0 MHz to 20 MHz	-	57	-	dB	
		20 MHz to 100 MHz	-	39	-	dB	
		minimum gain; V _{DDD}					
		0 MHz to 20 MHz	-	67	-	dB	
		20 MHz to 100 MHz	-	51	-	dB	
CMRR	common mode rejection	0 MHz to 20 MHz	-	75	-	dB	
	ratio	20 MHz to 100 MHz	-	45	-	dB	
Analog inpu	ts						
V _{i(p-p)(max)}	maximum peak-to-peak	minimum gain	-	1.0	-	V	
input voltage		maximum gain	-	60.4	-	mV	
V _{i(cm)}	common-mode input voltage		2.0	2.7	V _{DDA} – 1.9	V	
li	input current	V _{i(cm)} = 2.7 V	-	55	-	μA	
R _i	input resistance		10	-	-	kΩ	
C _i	input capacitance		-	-	5	pF	
Analog outp	outs[2]						
V _{o(dif)(p-p)max}	maximum peak-to-peak	maximum gain	2.0	-	-	V	
	differential output voltage	minimum gain	2.0	-	-	V	
V _{O(cm)}	common-mode output voltage	referenced to V _{DDA} ; T _{amb} = 25 °C	V _{DDA} – 2.56	V _{DDA} - 2.42	V _{DDA} – 2.29	V	
ΔV _{O(cm)} /ΔT	common-mode output voltage variation with temperature		-	-1.8	-	mV/°C	
SR _{se}	single-ended slew rate		-	275	-	V/µs	
R _o	output resistance		-	15	26	Ω	
Co	output capacitance		-	3	-	pF	
Variable gai	n amplifier dynamic perf	ormance; $C_L = 5 \text{ pF}; R_L = 6$	680 Ω; see Figure	6, <u>7</u> , <u>8</u> , <u>9</u> and	10		
α _{2H}	second harmonic level	$V_o = V_{o(max)}$					
		$f_i = 0.5 \text{ MHz}$	-	-80	-67	dBc	
		f _i = 4.43 MHz	-	-77	-67	dBc	
		f _i = 12.5 MHz	-	-76	-65	dBc	
		· · · · · · · · · · · · · · · · · · ·		· -			

Table 6. Characteristics ...continued

 $V_{DDA} = V11$ to V12 = 4.75 V to 5.25 V; $V_{DDD} = V18$ to V17 = 3.0 V to 5.25 V; V_{SSA} and V_{SSD} shorted together; $T_{amb} = -40$ °C to +85 °C; typical values measured at $V_{CCA} = 5.0$ V; $V_{CCD} = 3.3$ V and $T_{amb} = 25$ °C unless otherwise specified [1].

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
α _{3H}	third harmonic level	$V_o = V_{o(max)}$; $T_{amb} = 25 \ ^{\circ}C$					
		$f_i = 0.5 \text{ MHz}$		-	-64	-60	dBc
		f _i = 4.43 MHz		-	-64	-59	dBc
		f _i = 12.5 MHz		-	-62	-58	dBc
		f _i = 21.4 MHz		-	-61	-57	dBc
$\Delta \alpha_{3H} / \Delta T$	third harmonic level variation with temperature	f _i = 21.4 MHz		-	80	-	mdB/°C
Reference v	voltage output ADC: pin 0	CMADC					
V _{ref}	reference voltage	referenced to V_{DDA} ; T _{amb} = 25 °C		V _{DDA} - 1.64	V _{DDA} – 1.45	V _{DDA} – 1.26	V
Ro	output resistance	T _{amb} = 25 °C		-	17	26	Ω
$\Delta V_{o(ref)} / \Delta T$	reference output voltage variation with temperature			-	-0.11	-	mV/°C
I _{o(max)}	maximum output current			-	1.0	-	mA
Co	output capacitance			-	3	-	pF
Reference v	voltage output VGA: pin C	MVGA					
V _{ref}	reference voltage	referenced to V _{DDA} ; T _{amb} = 25 °C		$V_{DDA}-2.48$	$V_{DDA}-2.30$	V _{DDA} – 2.17	V
Ro	output resistance	$T_{amb} = 25 \ ^{\circ}C$		-	9	20	Ω
$\Delta V_{o(ref)} / \Delta T$	reference output voltage variation with temperature			-	1.75	-	mV/°C
I _{o(max)}	maximum output current			-	1.0	-	mA
Co	output capacitance			-	3	-	pF
Gain switch	ning characteristics (in la	tched mode); f _{clk} = 52 MHz	; T _{am}	_b = 25 °C; see	e <mark>Figure 3</mark>		
t _h	hold time			2.0	-	-	ns
t _{su}	set-up time			3.8	-	-	ns
t _w	pulse width			5.8	-	-	ns
t _{PD}	propagation delay			-	4.2	5.9	ns
t _s	settling time	10 % to 90 % full scale if ±6 dB gain change	<u>[3]</u>	-	2.6	3.2	ns
Gain switch	ning characteristics (in tra	ansparent mode); f _{clk} = 52	MHz;	T _{amb} = 25 °C	; see <mark>Figure</mark>	4	
t _{PD}	propagation delay			-	6.7	9.5	ns
t _s	settling time	10 % to 90 % full scale if ±6 dB gain change	<u>[4]</u>	-	5.4	6.9	ns
Clock timin	g input: pins CLK and CL	.KN (see <u>Figure 3</u>)					
f _{clk(max)}	maximum clock frequency			52	-	-	MHz
t _{w(clk)L}	LOW clock pulse width			4.0	-	-	ns
t _{w(clk)H}	HIGH clock pulse width			4.0	-	-	ns
DA9901_4						© NXP B.V. 2008.	All rights rese

Table 6. Characteristics ...continued

 $V_{DDA} = V11$ to V12 = 4.75 V to 5.25 V; $V_{DDD} = V18$ to V17 = 3.0 V to 5.25 V; V_{SSA} and V_{SSD} shorted together; $T_{amb} = -40$ °C to +85 °C; typical values measured at $V_{CCA} = 5.0$ V; $V_{CCD} = 3.3$ V and $T_{amb} = 25$ °C unless otherwise specified [1]

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _r	rise time			-	4.0	-	ns
t _f	fall time			-	4.0	-	ns
Digital inp	uts: pins TE, GRAY0, GRA	Y1 and GRAY2					
V _{IL}	LOW-level input voltage			0	-	0.8	V
V _{IH}	HIGH-level input voltage			2.0	-	V _{DDD}	V
I _{IH}	HIGH-level input current			-10	-	+10	μA
IIL	LOW-level input current			-10	-	+10	μΑ
Ci	input capacitance			-	-	3	pF
Clock inpu	its in TTL mode						
V _{IL}	LOW-level input voltage		[5]	0	-	0.8	V
V _{IH}	HIGH-level input voltage		[5]	2.0	-	V _{DDD}	V
I _{IH}	HIGH-level input current			15	-	80	μΑ
I _{IL}	LOW-level input current			-40	-	-10	μΑ
Ci	input capacitance			-	-	2	pF
Clock inpu	its in differential mode						
VIL	LOW-level input voltage	$V_{DDA} = 5.0 V$	[6]	3.19	-	3.52	V
VIH	HIGH-level input voltage	$V_{DDA} = 5.0 V$	[6]	3.83	-	4.12	V
I _{IH}	HIGH-level input current			15	-	80	μΑ
I _{IL}	LOW-level input current			-40	-	-5	μΑ
Ci	input capacitance			-	-	2	pF
V _{i(dif)(p-p)}	peak-to-peak differential input voltage	DC voltage level = 2.5 V		0.1	-	2.0	V

[1] Due to the behavior of the on-chip regulator a warm-up time of 1 minute (typical) is recommended for optimal performance.

[2] The analog output voltages are positive with respect to V_{SSA}.

[3] In latching mode (pin TE LOW), the gain settling is latched at the rising edge of the clock input.

[4] In transparent mode, the gain settling is directly controlled by the input data pattern.

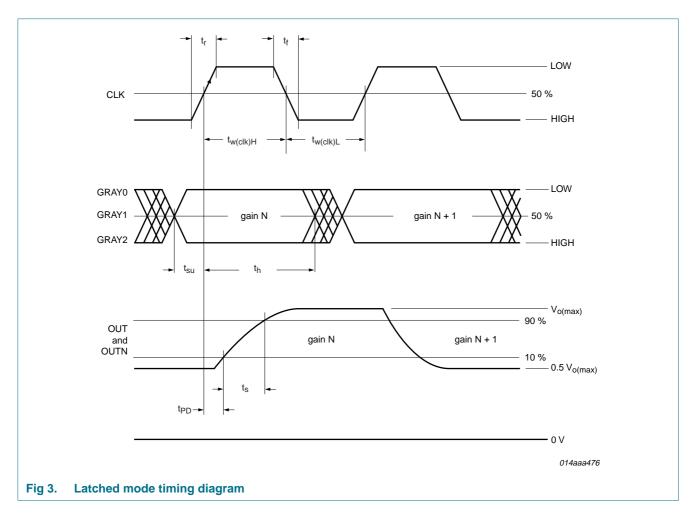
[5] The circuit may be used with a single TTL clock on CLK or CLKN. The unused clock pin has to be decoupled to ground with a 100 nF capacitance.

[6] There are four modes of operation for the clock inputs in non-TTL mode:

- a) PECL mode 1: (DC level vary 1 : 1 with V_{DDA}) CLK and CLKN inputs are differential PECL levels.
- b) PECL mode 2: (DC level vary 1 : 1 with V_{DDA}) CLK input is at PECL level and gain change takes place on the rising edge of the clock input signal when in latched mode. A DC level of 3.65 V has to be applied on CLKN decoupled to V_{SSD} via a 100 nF capacitor.
- c) PECL mode 3: (DC level vary 1 : 1 with V_{DDA}) CLKN input is at PECL level and gain change takes place on the rising edge of the clock input signal when in latched mode. A DC level of 3.65 V has to be applied on CLK decoupled to V_{SSD} via a 100 nF capacitor.
- d) AC driving mode 4: when driving the CLK input directly and with any AC signal of minimum 0.1 V (p-p) and with a DC level of 2.5 V, the gain change takes place on the rising edge of the clock signal. When driving the CLKN input with the same signal, gain change takes place on the falling edge of the clock signal. NXP Semiconductors recommends decoupling of the CLKN or CLK input to V_{SSD} via a 100 nF capacitor.

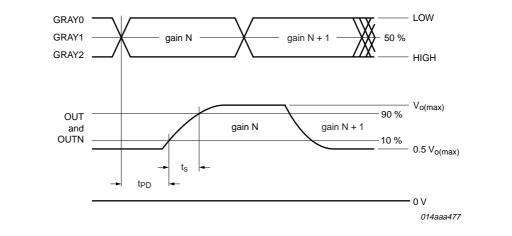
12. Additional information relating to Table 6

State	Gray input data code			Gain (dB)
Otate	-	-		
	Pins Gray2, Gray1, Gray0			
	D2	D1	D0	
0	0	0	0	minimum
1	0	0	1	minimum + 6
2	0	1	1	minimum + 12
3	0	1	0	minimum + 18
4	1	1	0	minimum + 24
other	-	-	-	minimum + 24

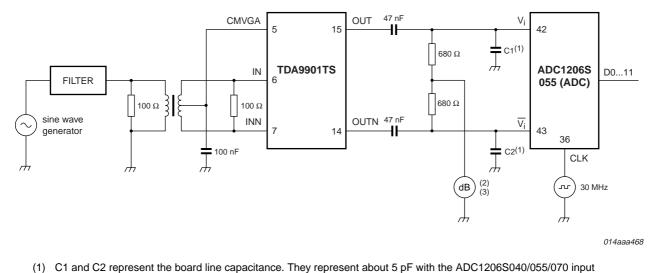


TDA9901

Wideband differential digital controlled variable gain amplifier





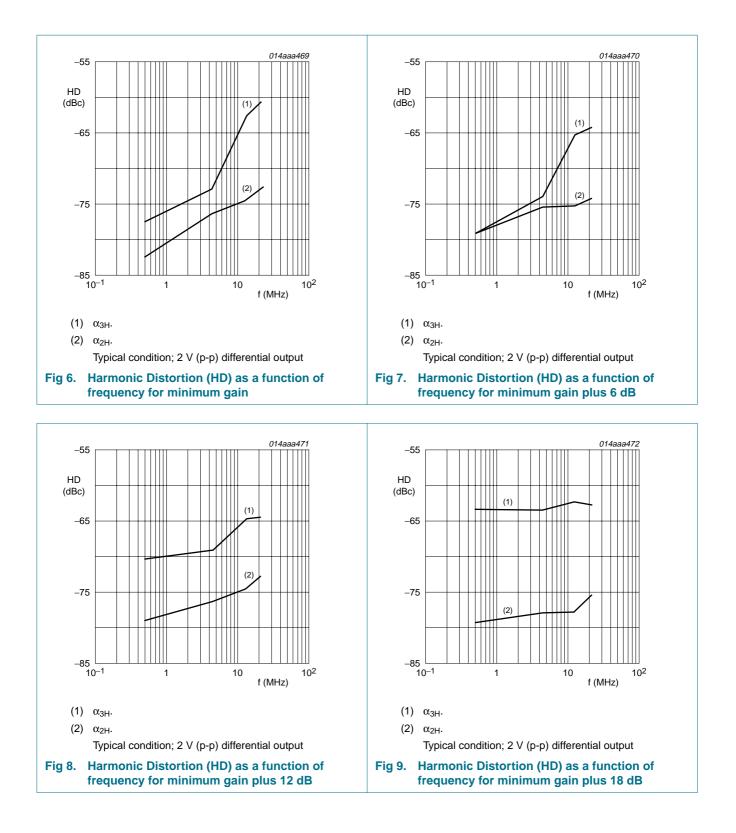


- capacitance. Special care has to be taken to minimize this load in order to have the best dynamic performance.
- (2) The α_{2H} and α_{3H} of the ADC1206S040/055/070 is lower than that measured on the TDA9901. This measurement method is preferred to conventional methods due to its low contribution to the α_{2H} .
- (3) The chain measurement shows the harmonic distortion of the TDA9901 as the measurement from ADC1206S040/055/070 is negligible.

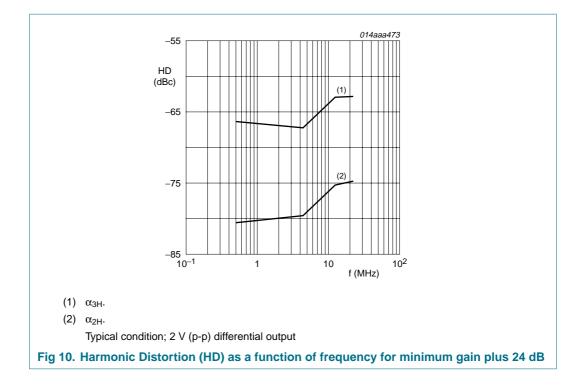
Fig 5. Dynamic distortion measurement diagram

TDA9901

Wideband differential digital controlled variable gain amplifier

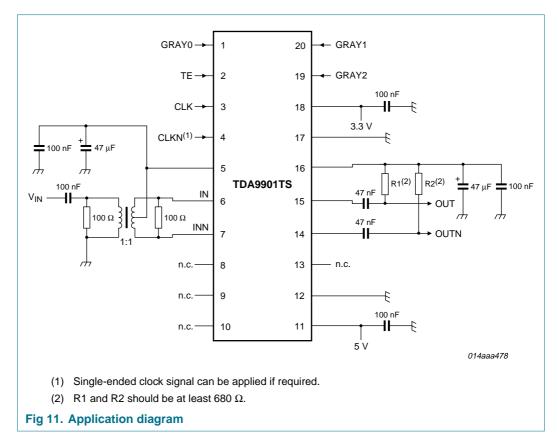


Wideband differential digital controlled variable gain amplifier



13. Application information

13.1 Application diagrams



13.2 Recommended companion chip

Table 8. Recommended companion chips

Type number	Description	Sampling frequency
ADC1006S055	Single 10 bits ADC	55 MHz
ADC1006S070	Single 10 bits ADC	70 MHz
ADC1206S040	Single 12 bits ADC	40 MHz
ADC1206S055	Single 12 bits ADC	55 MHz
ADC1206S070	Single 12 bits ADC	70 MHz

Wideband differential digital controlled variable gain amplifier

14. Package outline

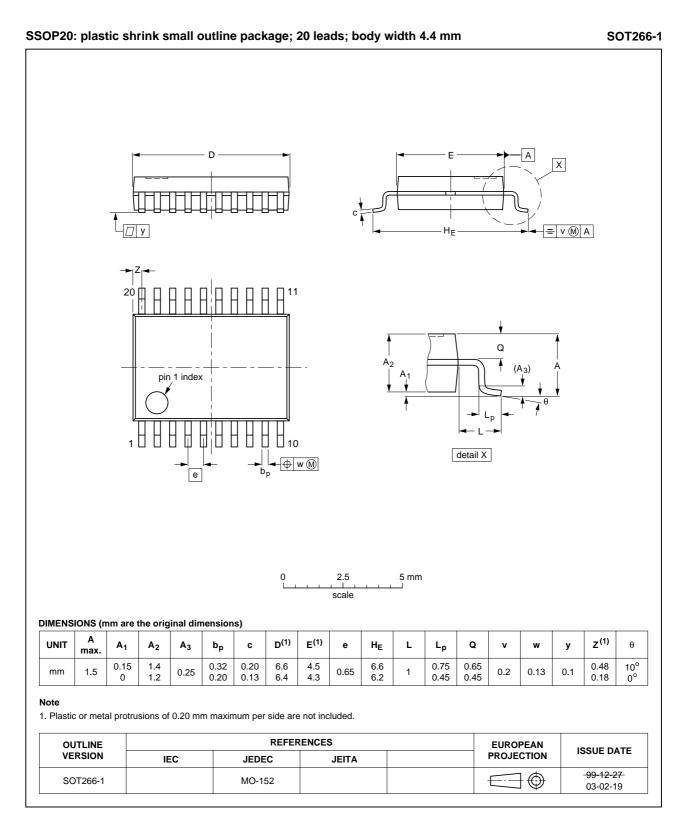


Fig 12. Package outline SOT266-1 (SSOP20)

15. Revision history

Table 9.Revision	history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
TDA9901_4	20080814	Product data sheet	-	TDA9901_3	
Modifications: • Correction made to ΔV_{DD} conditions in <u>Table 4</u> .					
 Corrections made to values of t_{d(grp)} and G_{step} in <u>Table 6</u>. 					
TDA9901_3	20080611	Product specification	-	TDA9901_2	
TDA9901_2	19991008	Product specification	-	TDA9901_N_1	
TDA9901_N_1	19980415	Product specification	-	-	

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

16.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

16.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

17. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

TDA9901

Wideband differential digital controlled variable gain amplifier

18. Contents

1	General description 1
2	Features 1
3	Applications 1
4	Quick reference data 2
5	Ordering information 2
6	Block diagram 3
7	Pinning information 4
7.1	Pinning 4
7.2	Pin description 4
8	Functional description 5
9	Limiting values 5
10	Thermal characteristics 5
11	Characteristics 6
12	Additional information relating to Table 6 10
13	Application information
13.1	Application diagrams 14
13.2	Recommended companion chip 14
14	Package outline 15
15	Revision history 16
16	Legal information 17
16.1	Data sheet status 17
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks 17
17	Contact information 17
18	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2008.

All rights reserved.



founded by

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 14 August 2008 Document identifier: TDA9901_4